

Strong-Coupling Model for Pulsed Light Propagation and Quantum Kinetics of Electron-Hole Plasmas in Quantum Wire Arrays

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Abstract: A quantum-kinetic model is proposed for ultrafast carrier-scattering dynamics in quantum wires coupled to resonant scattering of ultrashort light pulses. The model includes effects from transverse, longitudinal, and applied DC fields on the wires.

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1. Introduction

A self-consistent quantum-kinetic model is proposed for studying the strong coupling between ultrafast carrier-scattering dynamics of photo-excited electron-hole plasmas in quantum wires and the resonant scattering of an ultrashort light pulse incident on a quantum wire array. The individual electron and hole distributions in momentum space are further driven by an applied DC electric field along the wires, including a resistive force for momentum relaxation due to intrinsic phonon and Coulomb scattering of photo-excited carriers. The combination of an applied DC field with a localized longitudinal electromagnetic field is able to effectively modify an induced transverse polarization field as a quantum back-action of electrons on the propagating light pulse. This strong-coupling model allows us to study the correlation between the localized electronic response of quantum wires and the spatial-temporal features and phases of the scattered light pulses. Additionally, this strong-coupling theory can also reveal a unique correlation between the DC current from the driven electron-hole plasma and the localized longitudinal electromagnetic field due to induced long-lasting plasma oscillations in quantum wires.

2. Theory

2.1. Pulse Propagation

A 2D near-IR laser pulse electric field $\mathbf{E}(x, y, t)$ is initially polarized primarily in the x -direction, the magnetic field is purely in the z -direction $\mathbf{H}(x, y, t)$, and is propagating in the y -direction along the quantum wire as shown in Fig. 1. The propagation is simulated by solving the Maxwell equations for the electric and magnetic fields in a non-magnetic medium. For this, a Pseudo-Spectral Time Domain method is used that casts the Maxwell equations in the Fourier transformed wave-vector (\mathbf{q}) space. [1]

2.2. Laser-Semiconductor Plasma Interaction

For photo-excited spin-degenerated electrons and holes in the j th quantum wire, the quantum-kinetic semiconductor Bloch equations are given by [2–4]

$$\frac{dn_{j,k}^e(t)}{dt} = \frac{2}{\hbar} \sum_{k'} \text{Im} \{ \mathbf{p}_{j,k,k'}(t) \cdot \mathbf{Q}_{j,k',k}(t) \} + \left. \frac{\partial n_{j,k}^e(t)}{\partial t} \right|_{\text{rel}}, \quad (1)$$

$$\frac{dn_{j,k'}^h(t)}{dt} = \frac{2}{\hbar} \sum_k \text{Im} \{ \mathbf{p}_{j,k,k'}(t) \cdot \mathbf{Q}_{j,k',k}(t) \} + \left. \frac{\partial n_{j,k'}^h(t)}{\partial t} \right|_{\text{rel}}, \quad (2)$$

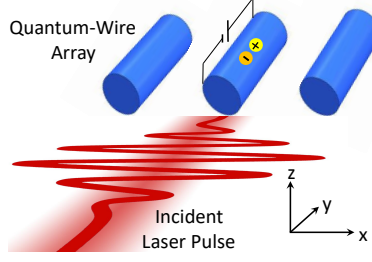


Fig. 1. Illustration of a light pulse propagating within a dielectric layer along the quantum-wire array.

$$i\hbar \frac{d\mathbf{p}_{j,k,k'}(t)}{dt} = \left[\boldsymbol{\varepsilon}_k^e + \boldsymbol{\varepsilon}_{k'}^h + \varepsilon_G + \Delta\boldsymbol{\varepsilon}_{j,k}^e + \Delta\boldsymbol{\varepsilon}_{j,k'}^h - i\hbar\Delta_{j,k,k'}^{eh}(t) \right] \mathbf{p}_{j,k,k'}(t) - \left[1 - n_k^e(t) - n_{k'}^h(t) \right] \mathbf{Q}_{j,k,k'}(t) \quad (3)$$

$$+ i\hbar \sum_{q \neq 0} \Lambda_{j,k,q}^e(t) \mathbf{p}_{j,k+q,k'}(t) + i\hbar \sum_{q' \neq 0} \Lambda_{j,k',q'}^h(t) \mathbf{p}_{j,k,k'+q'}(t),$$

where $\mathbf{p}_{j,k,k'}(t) = \sum_{\sigma=x,y} p_{j,k,k'}^\sigma(t) \hat{\mathbf{e}}_{\mathbf{d}}^\sigma$ is the microscopic polarization, $\mathbf{Q}_{j,k,k'}(t) = \sum_{\sigma=x,y} Q_{j,k,k'}^\sigma(t) \hat{\mathbf{e}}_{\mathbf{d}}^\sigma$ is the renormalized Rabi frequency, $n_{j,k}^e(t)$ and $n_{j,k'}^h(t)$ are the electron (e) and hole (h) occupation numbers at momenta $\hbar k$, and $\hbar k'$, respectively. In Eq. (3) ε_G is the wire bandgap, $\boldsymbol{\varepsilon}_{j,k}^e$ and $\boldsymbol{\varepsilon}_{j,k'}^h$ are the kinetic energies of electrons and holes, $\Delta\boldsymbol{\varepsilon}_{j,k}^e$ and $\Delta\boldsymbol{\varepsilon}_{j,k'}^h$ are the Coulomb renormalization [5] of the kinetic energies of electrons and holes, $\Delta_{j,k,k'}^{eh}(t) = \Delta_{j,k}^e(t) + \Delta_{j,k'}^h(t)$ is the diagonal dephasing rate [6] (quasi-particle lifetime), while $\Lambda_{j,k,q}^e(t)$ and $\Lambda_{j,k',q'}^h(t)$ are the off-diagonal dephasing rates [6] (pair-scattering) for electrons and holes. The Boltzmann relaxation terms in Eqs. (1) and (2) contain carrier-carrier Coulomb scattering, carrier-phonon scattering, and a drift term resulting from an applied DC field. From these solutions we calculate the 1D wire polarization [7] for use in the Maxwell Equations:

$$\tilde{\mathbf{P}}_{\text{qw}}(\mathbf{q}, t) = \sum_{\sigma=x,y} \tilde{P}_{\text{qw}}^\sigma(\mathbf{q}, t) \hat{\mathbf{e}}_{\mathbf{d}}^\sigma = \sum_j e^{-iq_x x_j^\perp - q_x^2/4\alpha^2} \sum_{\sigma=x,y} \tilde{P}_j^\sigma(q_y, t) \hat{\mathbf{e}}_{\mathbf{d}}^\sigma, \quad (4a)$$

$$\tilde{P}_j^\sigma(q_y, t) = \frac{d_{\text{cv}}\alpha}{2\delta_0\mathcal{L}} \sum_k p_{j,k+q_y,k}^\sigma(t) + \text{H.C.}, \quad (4b)$$

where $\mathbf{p}_{j,k+q_y,k}(t)$ is determined by Eq. (3), x_j^\perp is the transverse position of the j th quantum wire, δ_0 is the thickness of each quantum wire, d_{cv} is the 2D isotropic dipole moment between the valence and conduction band, and H.C. stands for the Hermitian conjugate term. The 1D free-charge density distribution in the wire is given for the Maxwell equations by $\tilde{\rho}_j^{\text{ID}}(q_y, t) = \tilde{\rho}_j^{\text{h}}(q_y, t) + \tilde{\rho}_j^{\text{e}}(q_y, t)$, where $\tilde{\rho}_j^{\text{h}}(q_y, t)$ and $\tilde{\rho}_j^{\text{e}}(q_y, t)$ are the charge-density distributions of holes and electrons in the j th quantum wire, which we calculate within the random-phase approximation [8].

References

1. A. Taflove and S. C. Hagness, *Computational Electrodynamics: The Finite-Difference Time-Domain Method* (Artech House, Inc., 2000), 3rd ed.
2. H. Haug and S. W. Koch, *Quantum Theory of the Optical and Electronic Properties of Semiconductors* (World Scientific Publishing Co. Pte. Ltd., 2009), 5th ed.
3. J. R. Kuklinski and S. Mukamel, "Generalized semiconductor Bloch equations: Local fields and transient gratings," *Phys. Rev. B* **44**, 11,253–11,259 (1991).
4. R. Buschlingern, M. Lorke, and U. Peschel, "Light-matter interaction and lasing in semiconductor nanowires: A combined finite-difference time-domain and semiconductor Bloch equation approach," *Phys. Rev. B* **91**, 045,203 (2015).
5. D. H. Huang and M. O. Manasreh, *Physical Review B* **54**, 5620–5628 (1996).
6. M. Lindberg and S. W. Koch, "Effective Bloch equations for semiconductors," *Phys. Rev. B* **38**, 3342 (1988).
7. A. Iurov, D. H. Huang, G. Gumbs, W. Pan, and A. A. Maradudin, *Physical Review B* **96**, 081,408(R) (2017).
8. G. Gumbs and D. H. Huang, *Properties of Interacting Low-Dimensional Systems* (John Wiley & Sons, 2011).